





bq24001 bq24002 bq24003

SLUS462E - SEPTEMBER 2000 - REVISED NOVEMBER 2004

SINGLE-CELL LI-ION CHARGE MANAGEMENT IC FOR PDAS AND INTERNET APPLIANCES

FEATURES

- Highly Integrated Solution With FET Pass Transistor and Reverse-Blocking Schottky and Thermal Protection
- Integrated Voltage and Current Regulation
 With Programmable Charge Current
- High-Accuracy Voltage Regulation (±1%)
- Ideal for Low-Dropout Linear Charger Designs for Single-Cell Li-Ion Packs With Coke or Graphite Anodes
- Up to 1.2-A Continuous Charge Current
- Safety-Charge Timer During Preconditioning and Fast Charge
- Integrated Cell Conditioning for Reviving Deeply Discharged Cells and Minimizing Heat Dissipation During Initial Stage of Charge
- Optional Temperature or Input-Power Monitoring Before and During Charge
- Various Charge-Status Output Options for Driving Single, Double, or Bicolor LEDs or Host-Processor Interface
- Charge Termination by Minimum Current and Time
- Low-Power Sleep Mode
- Packaging: 5 mm × 5 mm MLP or 20-Lead TSSOP PowerPAD™

APPLICATIONS

- PDAs
- Internet Appliances
- MP3 Players
- Digital Cameras

DESCRIPTION

The bq2400x series ICs are advanced Li-Ion linear charge management devices for highly integrated and space-limited applications. They combine high-accuracy current and voltage regulation; FET pass-transistor and reverse-blocking Schottky; battery conditioning, temperature, or input-power monitoring; charge termination; charge-status indication; and charge timer in a small package.

The bg2400x measures battery temperature using an external thermistor. For safety reasons, the bg2400x inhibits charge until the battery temperature is within the user-defined thresholds. Alternatively, the user can monitor the input voltage to qualify charge. The bq2400x series then charge the battery in three phases: preconditioning, constant current, and constant voltage. If the battery voltage is below the internal low-voltage threshold, the bq2400x uses low-current precharge to condition the battery. A preconditioning timer is provided for additional safety. Following preconditioning, the bq2400x applies a constant-charge current to the battery. An external sense-resistor sets the magnitude of the current. The constant-current phase is maintained until the battery reaches the charge-regulation voltage. The bg2400x then transitions to the constant voltage phase. The user can configure the device for cells with either coke or graphite anodes. The accuracy of the voltage regulation is better than ±1% over the operating junction temperature and supply voltage range.

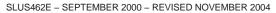
Charge is terminated by maximum time or minimum taper current detection

The bq2400x automatically restarts the charge if the battery voltage falls below an internal recharge threshold.

A

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.







These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

	PACK		
TJ	20-LEAD HTTSOP PowerPAD™ (PWP)(1)	20-LEAD 5 mm × 5 mm MLP (RGW) ⁽²⁾	CHARGE STATUS CONFIGURATION
	bq24001PWP	bq24001RGW	Single LED
-40°C to 125°C	bq24002PWP	bq24002RGW	2 LEDs
	bq24003PWP	bq24003RGW	Single bicolor LED

⁽¹⁾ The PWP package is available taped and reeled. Add R suffix to device type (e.g. bq24001PWPR) to order. Quantities 2500 devices per reel. (2) The RGW package is available taped and reeled. Add R suffix to device type (e.g. bq24001RGWR) to order. Quantities 3000 devices per reel.

PACKAGE DISSIPATION RATINGS

PACKAGE	ΘЈА	ΘJC	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C
PWP(1)	30.88°C/W	1.19°C/W	3.238 W	0.0324W/°C
RGW(2)	31.41°C/W	1.25°C/W	3.183 W	0.0318W/°C

⁽¹⁾ This data is based on using the JEDEC high-K board and topside traces, top and bottom thermal pad $(6.5 \times 3.4 \text{ mm})$, internal 1 oz power and ground planes, 8 thermal via underneath the die connecting to ground plane.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

	bq24001 bq24002 bq24003
Supply voltage (Vcc with respect to GND)	13.5 V
Input voltage (IN, ISNS, EN, APG/THERM/CR/STAT1/STAT2, VSENSE, TMR SEL, VSEL) (all with respect to GND)	13.5 V
Output current (OUT pins)	2 A
Output sink/source current (STAT1 and STAT2)	10 mA
Operating free-air temperature range, T _A	-40°C to 70°C
Storage temperature range, T _{Stg}	-65°C to 150°C
Junction temperature range, T _J	-40°C to 125°C
Lead temperature (Soldering, 10 sec)	300°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

	MIN	MAX	UNIT
Supply voltage, V _{CC}	4.5	10	V
Input voltage, VIN	4.5	10	V
Continuous output current		1.2	Α
Operating junction temperature range, TJ	-40	125	°C

⁽²⁾ This data is based on using the JEDEC high-K board and topside traces, top and bottom thermal pad (3.25 × 3.25 mm), internal 1 oz power and ground planes, 9 thermal via underneath the die connecting to ground plane.



ELECTRICAL CHARACTERISTICS

over recommended operating junction temperature supply and input voltages, and V_I (V_{CC}) $\geq V_I$ (IN) (unless otherwise noted)

PARAMETER	TEST CONDITIONS		TYP	MAX	UNIT
V _{CC} current	$V_{CC} > V_{CC}UVLO$, $EN \le V_{IH}(EN)$			1	mA
V _{CC} current, standby mode	$EN \le V_{IL}(EN)$		1		μΑ
IN current, standby mode	$EN \le V_{IL}(EN)$			10	μΑ
Standby current (sum of currents into OUT	$V_{CC} < V_{CC}$ _UVLO, $V_{OUT} = 4.3 \text{ V}$, $V_{SENSE} = 4.3 \text{ V}$		2	4	^
and VSENSE pins)	EN <= Vilen, VOUT = 4.3 V, VSENSE = 4.3 V		2	4	μΑ

VOLTAGE REGULATION, 0° C \leq T _J \leq 125 $^{\circ}$ C							
PARAMETER	TE	ST CONDITIONS		MIN	TYP	MAX	UNIT
Output voltage	VSEL = V _{SS} ,	0 < I _O ≤ 1.2 A		4.059	4.10	4.141	V
Output voltage	$VSEL = V_{CC}$	0 < I _O ≤ 1.2 A		4.158	4.20	4.242	V
Load regulation	$\begin{array}{c} 1 \text{ mA} \leq I_{\mbox{\scriptsize O}} \leq 1.2 \text{ A}, \\ V_{\mbox{\scriptsize CC}} = 5 \text{ V}, \end{array}$	V _{I(IN)} = 5 V, T _J = 25°C			1		mV
Line regulation	VOUT+VDO+Vilim(MA	X) < V _I (VCC) < 10 V, 7	Г _Ј = 25°С		0.01		%/V
Dropout voltage = VI(IN)-Vout	I _O = 1.0 A,	4.9 V <v<sub>I(Vcc)< 10 V</v<sub>	V			0.7	V
	$I_O = 1.2 \text{ A}, V_{OUT} + V$	DO+VilimMAX <vi(vcc)< td=""><td>< 10 V</td><td></td><td></td><td>0.8</td><td>V</td></vi(vcc)<>	< 10 V			0.8	V

CURRENT REGULATION, 0° C \leq T _J \leq 125 $^{\circ}$ C						
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Current regulation threshold, V _{I(limit)}	VSENSE < VO(VSEL-LOW/HIGH)	0.095	0.1	0.105	V	
Delay time	VSENSE pulsed above VVLOWV to I _O = 10% of regulated value ⁽¹⁾			1	ms	
Rise time	I _O increasing from 10% to 90% of regulated value. R _{SNS} \geq 0.2 Ω , (1)	0.1		1	ms	

⁽¹⁾ Specified by design, not production tested.

CURRENT SENSE RESISTOR, 0°C ≤	Γ _J ≤ 125°C				
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
External current sense resistor range (RSNS)	100 mA ≤ Ilim ≤ 1.2 A	0.083		1	Ω

PRECHARGE CURRENT REGULATION, $0^{\circ}\text{C} \le \text{T}_{\text{J}} \le 125^{\circ}\text{C}$						
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Precharge current regulation	VSENSE <vlowv, <math="">0.083 \le R_{SNS} \le 1.0 \Omega</vlowv,>	40	60	80	mA	

V_{CC} UVLO COMPARATOR, $0^{\circ}C \le T_{J} \le 12$	25°C				
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Start threshold		4.35	4.43	4.50	V
Stop threshold		4.25	4.33	4.40	V
Hysteresis		50			mV

APG/THERM COMPARATOR, $0^{\circ}\text{C} \le \text{T}_{\text{J}} \le 125^{\circ}\text{C}$					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Upper trip threshold		1.480	1.498	1.515	V
Lower trip threshold		0.545	0.558	0.570	V
Input bias current				1	μΑ

LOWV COMPARATOR, $0^{\circ}C \le T_J \le 125$	°C				
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Start threshold		2.80	2.90	3.00	V
Stop threshold		3.00	3.10	3.20	V
Hysteresis		100			mV



ELECTRICAL CHARACTERISTICS CONTINUED

over recommended operating junction temperature supply and input voltages, and V_I (V_{CC}) $\geq V_I$ (IN) (unless otherwise noted)

HIGHV (RECHARGE) COMPARATOR, 0°C ≤	T _J ≤ 125°C						
PARAMETER		TEST CONDIT	TIONS	MIN	TYP	MAX	UNIT
Start threshold				3.80	3.90	4.00	V

OVERV COMPARATOR, 0° C \leq T $_{J}$ \leq 125 $^{\circ}$ C					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Start threshold		4.35	4.45	4.55	V
Stop threshold		4.25	4.30	4.35	V
Hysteresis		50			mV

TAPERDET COMPARATOR, $0^{\circ}C \le T_{J} \le 125^{\circ}C$	С				
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Trip threshold		12	18.5	25	mV

EN LOGIC INPUT, 0° C \leq T $_{J}$ \leq 125 $^{\circ}$ C					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
High-level input voltage		2.25			V
Low-level input voltage				0.8	V
Input pulldown resistance		100		200	kΩ

VSEL LOGIC INPUT, 0° C \leq T $_{J}$ \leq 125 $^{\circ}$ C					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
High-level input voltage		2.25			V
Low-level input voltage				0.8	V
Input pulldown resistance		100		200	kΩ

TMR SEL INPUT 0° C \leq T _J \leq 125 $^{\circ}$ C					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
High-level input voltage		2.7			V
Low-level input voltage				0.6	V
Input bias current	V _I (TMR SEL) ≤ 5V			15	μΑ

STAT1, STAT2 (bq24001, bq24003), 0	°C ≤ T _J ≤ 125°C				
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Output (low) saturation voltage	I _O = 10 mA			1.5	V
Output (low) saturation voltage	$I_O = 4 \text{ mA}$			0.6	V
Output (high) saturation voltage	$I_{O} = -10 \text{ mA}$	V _{CC} -1.5			V
Output (high) saturation voltage	$I_O = -4 \text{ mA}$	V _{CC} -0.5			V
Output turn on/off time	$I_O = \pm 10 \text{ mA}, C = 100 \text{ p}(1)$			100	μs

⁽¹⁾ Assured by design, not production tested.

POWER-ON RESET (POR), 0° C \leq T _J \leq 125 $^{\circ}$ C					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POR delay	See Note 1	1.2		3	ms
POR falling-edge deglitch	See Note 1	25		75	μs

⁽¹⁾ Assured by design, not production tested.



ELECTRICAL CHARACTERISTICS CONTINUED

over recommended operating junction temperature supply and input voltages, and V_I (V_{CC}) ≥ V_I (IN) (unless otherwise noted)

APG/THERM DELAY, $0^{\circ}\text{C} \le \text{T}_{\text{J}} \le 125^{\circ}\text{C}$					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
APG/THERM falling-edge deglitch	See Note 1	25		75	μs

⁽¹⁾ Assured by design, not production tested.

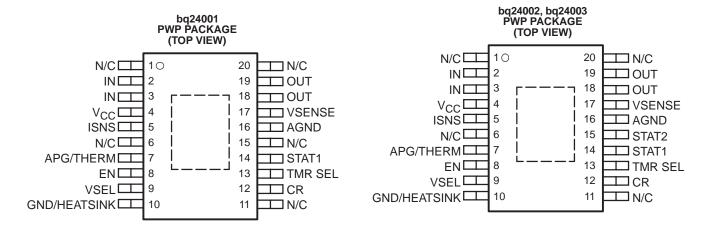
TIMERS, 0°C ≤ T _J ≤ 125°C					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
User-selectable timer accuracy	T _A = 25°C	-15%		15%	
		-20%		20%	
Precharge and taper timer			22.5		minute

THERMAL SHUTDOWN, $0^{\circ}C \le T_{J} \le 125^{\circ}C$					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Thermal trip	See Note 1		165		°C
Thermal hysteresis	See Note 1		10		°C

⁽¹⁾ Assured by design, not production tested.

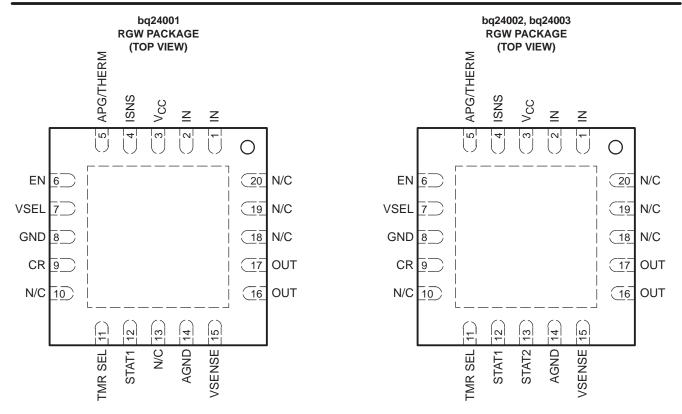
CR PIN, 0° C \leq T _J \leq 125 $^{\circ}$ C					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Output voltage	0 < I _{O(CR)} < 100 μA	2,816	2.85	2.88	V

PIN ASSIGNMENTS



N/C - Do not connect





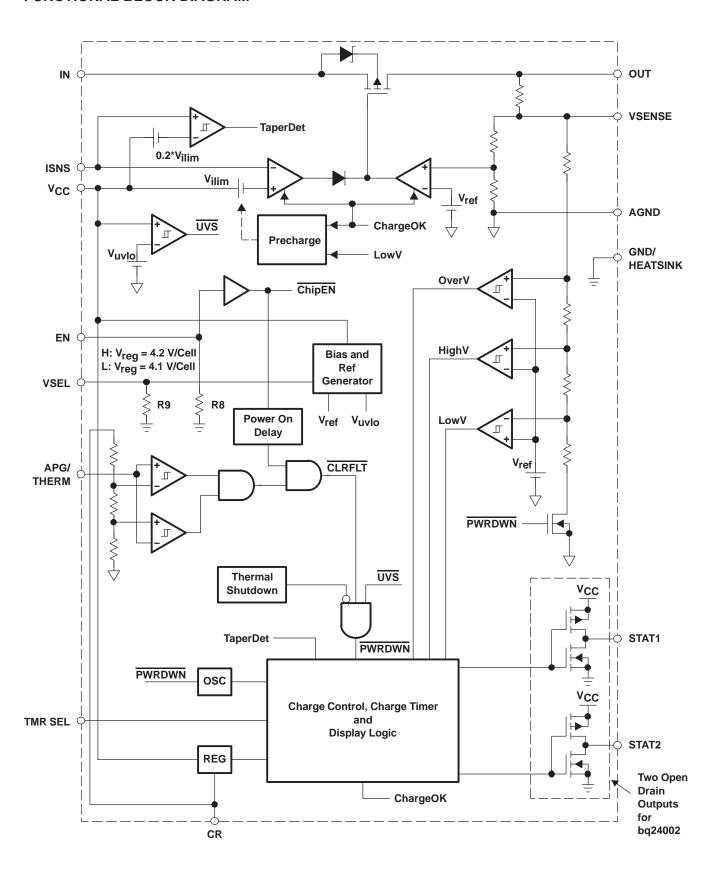
N/C - Do Not Connect

Terminal Functions

TERMINAL						
NAME	NO.	NO.	1/0	DESCRIPTION		
AGND	16	14		Ground pin; connect close to the negative battery terminal.		
APG/THERM	7	5	I	Adapter power good input/thermistor sense input		
CR	12	9	I	Internal regulator bypass capacitor		
EN	8	6	I	Charge-enable input. Active-high enable input with internal pull down. Low-current stand-by mode active when EN is low.		
GND/HEATSINK	10	8		Ground pin; connect to PowerPAD heat-sink layout pattern.		
IN	2, 3	1, 2	I	Input voltage. This input provides the charging voltage for the battery.		
ISNS	5	4	I	Current sense input		
N/C	1, 6, 11, 15, 20	10, 13, 18–20		No connect. These pins must be left floating. Pin 15 is N/C on bq24001PWP only. Pin 13 is N/C on bq24001RGW only.		
OUT	18, 19	16, 17	0	Charge current output		
STAT1	14	12	0	Status display output 1		
STAT2	15	13	0	Status display output 2 (for bq24002 and bq24003 only)		
TMR SEL	13	11	I	Charge timer selection input		
VCC	4	3	I	Supply voltage		
VSEL	9	7	I	4.1 V or 4.2 V charge regulation selection input		
VSENSE	17	15	I	Battery voltage sense input		

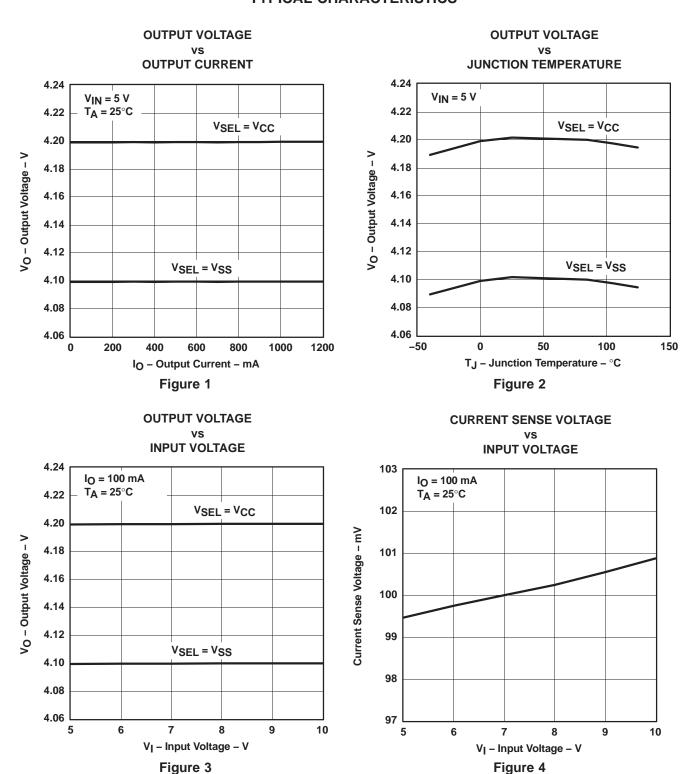


FUNCTIONAL BLOCK DIAGRAM



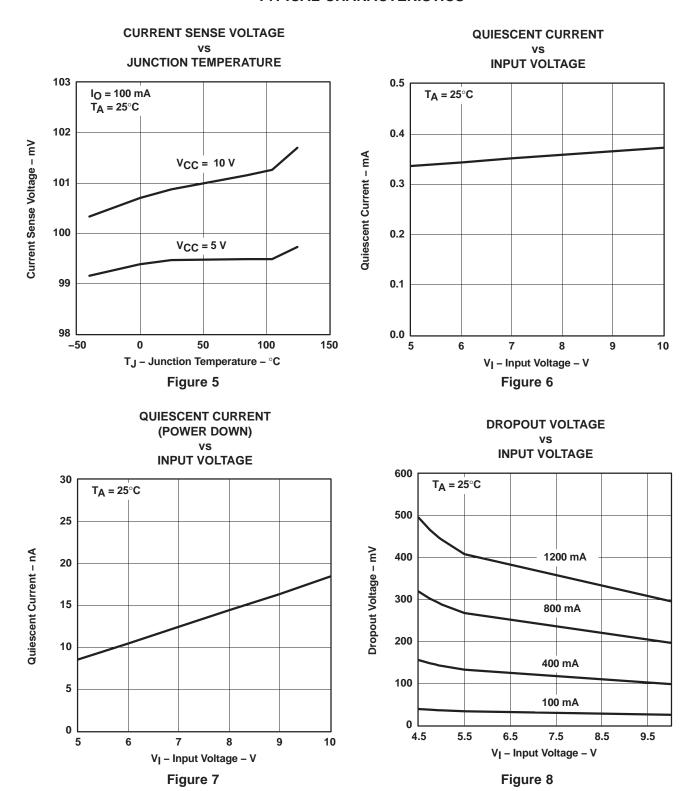


TYPICAL CHARACTERISTICS



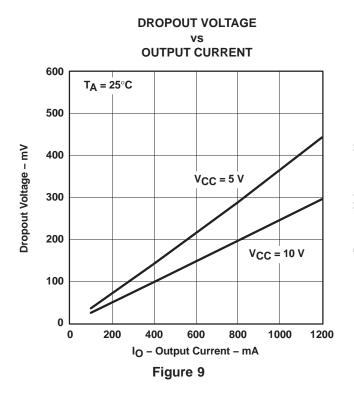


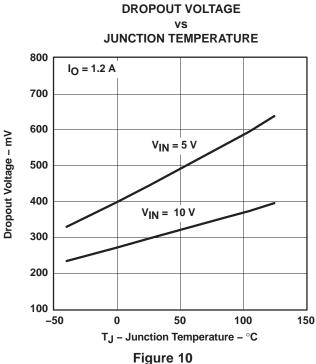
TYPICAL CHARACTERISTICS

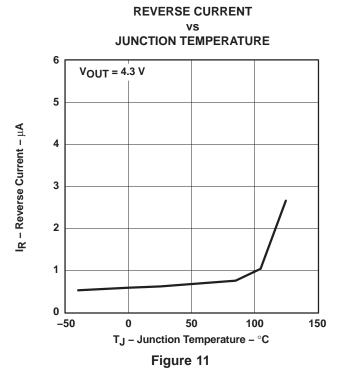


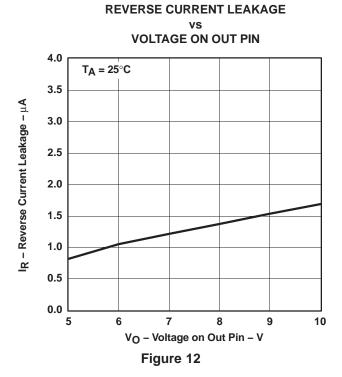


TYPICAL CHARACTERISTICS











APPLICATION INFORMATION

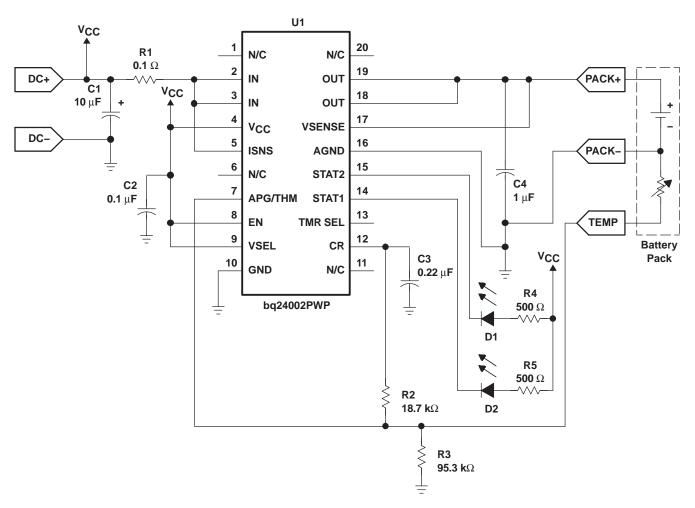


Figure 13. Li-Ion/Li-Pol Charger

- If the TMR SEL pin is left floating (3 HR time), a 10-pF capacitor should be installed between TMR SEL and CR.
- If a micro process is monitoring the STAT pins, it may be necessary to add some hysteresis into the feedback
 to prevent the STAT pins from cycling while crossing the taper detect threshold (usually less than one half
 second). See SLUU083 EVM or SLUU113 EVM for additional resistors used for the STAT pins.



APPLICATION INFORMATION

FUNCTIONAL DESCRIPTION

The bq2400x supports a precision current- and voltage-regulated Li-Ion charging system suitable for cells with either coke or graphite anodes. See Figure 14 for a typical charge profile and Figure 15 for an operational flowchart.

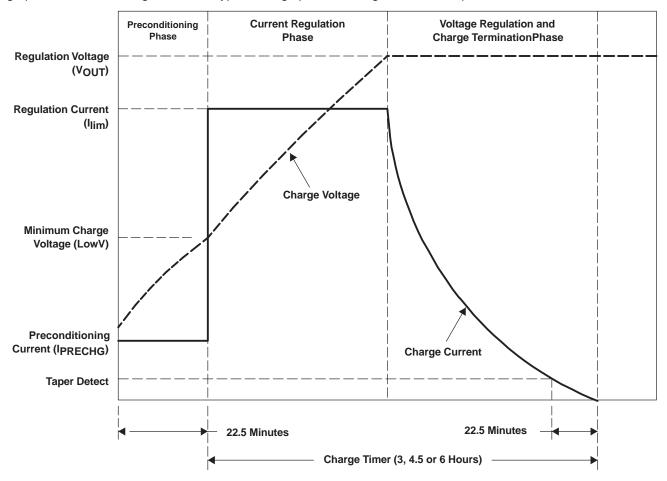


Figure 14. Typical Charge Profile



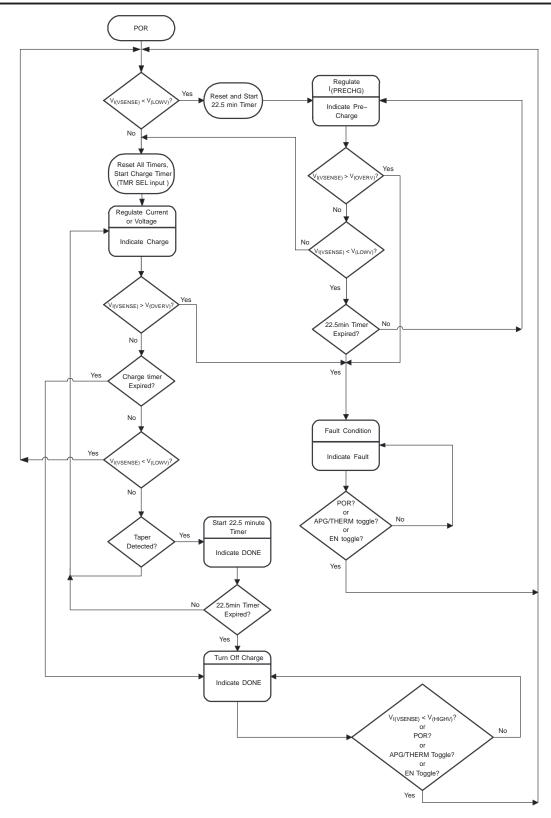


Figure 15. Operational Flow Chart



Charge Qualification and Preconditioning

The bq2400x starts a charge cycle when power is applied while a battery is present. Charge qualification is based on battery voltage and the APG/THERM input.

As shown in the block diagram, the internal LowV comparator output prevents fast-charging a deeply depleted battery. When set, charging current is provided by a dedicated precharge current source. The precharge timer limits the precharge duration. The precharge current also minimizes heat dissipation in the pass element during the initial stage of charge.

The APG/THERM input can also be configured to monitor

either the adapter power or the battery temperature using a thermistor. The bq2400x suspends charge if this input is outside the limits set by the user. Please refer to the APG/THERM input section for additional details.

APG/THERM Input

The bq400x continuously monitors temperature or system input voltage by measuring the voltage between the APG/THERM (adapter power good/thermistor) and GND. For temperature, a negative- or a positive- temperature coefficient thermistor (NTC, PTC) and an external voltage divider typically develop this voltage (see Figure 16). The bq2400x compares this voltage against its internal V_{TP1} and V_{TP2} thresholds to determine if charging is allowed. (See Figure 17.)

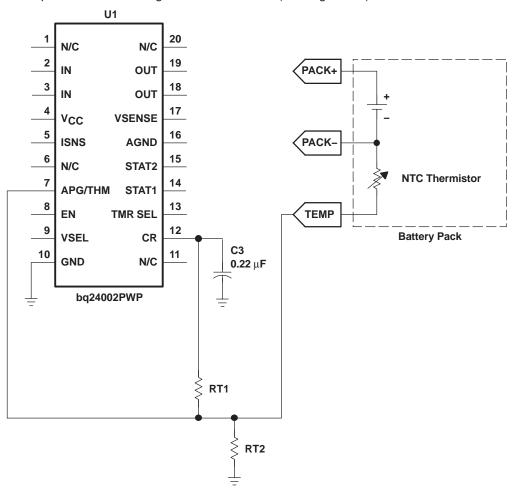


Figure 16. Temperature Sensing Circuit

bq24001



If the charger designs incorporate a thermistor, the resistor divider RT1 and RT2 is calculated by using the following two equations.

First, calculate RT2.

$$RT2 = \frac{V_B R_H R_C \left[\frac{1}{V_C} - \frac{1}{V_H}\right]}{R_H \left(\frac{V_B}{V_H} - 1\right) - R_C \left(\frac{V_B}{V_C} - 1\right)}$$

then use the resistor value to find RT1.

$$RT1 = \frac{\frac{V_B}{V_C} - 1}{\frac{1}{RT2} + \frac{1}{R_C}}$$

Temp Fault

V_{TP1}

Normal Temp Range

V_{TP2}

Temp Fault

GND

Figure 17. Temperature Threshold

Where:

 $V_B = V_{CR}$ (bias voltage)

 R_{H} = Resistance of the thermistor at the desired hot trip threshold

R_C = Resistance of the thermistor at the desired cold trip threshold

V_H = VP2 or the lower APG trip threshold

V_C = VP2 or the upper APG trip threshold

RT1 = Top resistor in the divider string

RT2 = Bottom resistor in the divider string

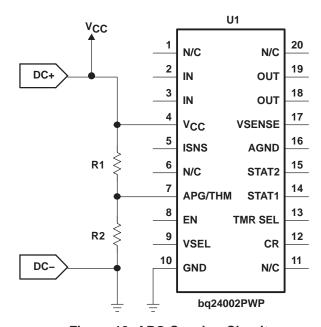


Figure 18. APG Sensing Circuit

Values of resistors R1 and R2 can be calculated using the following equation:

$$V_{APG} = V_{CC} \frac{R2}{(R1 + R2)}$$

where $V_{\mbox{\footnotesize{APG}}}$ is the voltage at the APG/THM pin.

Current Regulation

The bq2400x provides current regulation while the battery-pack voltage is less than the regulation voltage. The current regulation loop effectively amplifies the error between a reference signal, Vilim, and the drop across the external sense resistor, R_{SNS}.



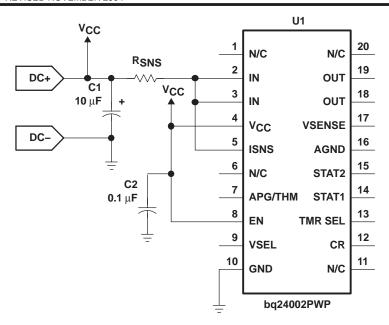


Figure 19. Current Sensing Circuit

Charge current feedback, applied through pin ISNS, maintains regulation around a threshold of Vilim. The following formula calculates the value of the sense resistor:

$$R_{SNS} = \frac{Vilim}{I_{REG}}$$

where I_{REG} is the desired charging current.

Voltage Monitoring and Regulation

Voltage regulation feedback is through pin VSENSE. This input is tied directly to the positive side of the battery pack. The bq2400x supports cells with either coke (4.1 V) or graphite (4.2 V) anode. Pin VSEL selects the charge regulation voltage.

VSEL State (see Note)	CHARGE REGULATION VOLTAGE		
Low	4.1 V		
High	4.2 V		

NOTE: VSEL should not be left floating.

Charge Termination

The bq2400x continues with the charge cycle until termination by one of the two possible termination conditions:

Maximum Charge Time: The bq2400x sets the maximum charge time through pin TMRSEL. The TMR SEL pin allows the user to select between three different total charge-time timers (3, 4, 5, or 6 hours). The charge timer is initiated after the preconditioning phase of the charge and is reset at the beginning of a new charge cycle. Note

that in the case of a fault condition, such as an out-of-range signal on the APG/THERM input or a thermal shutdown, the bg2400x suspends the timer.

TMRSEL STATE	CHARGE TIME	
Floating(1)	3 hours	
Low	6 hours	
High	4.5 hours	

(1) To improve noise immunity, it is recommended that a minimum of 10 pF capacitor be tied to Vss on a floating pin.

Minimum Current: The bq2400x monitors the charging current during the voltage regulation phase. The bq2400x initiates a 22-minute timer once the current falls below the taperdet trip threshold. Fast charge is terminated once the 22-minute timer expires.

Charge Status Display

The three available options allow the user to configure the charge status display for single LED (bq24001), two individual LEDs (bq24002) or a bicolor LED (bq24003). The output stage is totem pole for the bq24001 and bq24003 and open-drain for the bq24002. The following tables summarize the operation of the three options:

Table 1. bq24001 (Single LED)

CHARGE STATE	STAT1
Precharge	ON (LOW)
Fast charge	ON (LOW)
FAULT	Flashing (1 Hz, 50% duty cycle)
Done (>90%)	OFF (HIGH)
Sleep-mode	OFF (HIGH)
APG/Therm invalid	OFF (HIGH)
Thermal shutdown	OFF (HIGH)
Battery absent	OFF (HIGH)

bq24001



Table 2. bq24002 (2 Individual LEDs)

CHARGE STATE	STAT1 (RED)	STAT2 (GREEN)	
Precharge	ON (LOW)	OFF	
Fast charge	ON (LOW)	OFF	
FAULT	Flashing (1 Hz, 50% duty cycle)	OFF	
Done (>90%)	OFF	ON (LOW)	
Sleep-mode	OFF	OFF	
APG/Therm invalid	OFF	OFF	
Thermal shutdown	OFF	OFF	
Battery absent	OFF	OFF(1)	

⁽¹⁾ If thermistor is used, then the Green LED is off.

Table 3. bq24003 (Single Bicolor LED)

CHARGE STATE	LED1 (RED)	LED2 (GREEN)	APPARENT COLOR
Precharge	ON (LOW)	OFF (HIGH)	RED
Fast charge	ON (LOW)	OFF (HIGH)	RED
FAULT	ON (LOW)	ON (LOW)	YELLOW
Done (>90%)	OFF (HIGH)	ON (LOW)	GREEN
Sleep-mode	OFF (HIGH)	OFF (HIGH)	OFF
APG/Therm invalid	OFF (HIGH)	OFF (HIGH)	OFF
Thermal shutdown	OFF (HIGH)	OFF (HIGH)	OFF
Battery absent	OFF (HIGH)	OFF (HIGH) ⁽¹⁾	OFF(1)

⁽¹⁾ If thermistor is used, then the Green LED is off.

Thermal Shutdown

The bq2400x monitors the junction temperature T_J of the DIE and suspends charging if T_J exceeds 165°C. Charging resumes when T_J falls below 155°C.

DETAILED DESCRIPTION

POWER FET

The integrated transistor is a P-channel MOSFET. The power FET features a reverse-blocking Schottky diode, which prevents current flow from OUT to IN.

An internal thermal-sense circuit shuts off the power FET when the junction temperature rises to approximately 165°C. Hysteresis is built into the thermal sense circuit. After the device has cooled approximately 10°C, the power FET turns back on. The power FET continues to cycle off and on until the fault is removed.

CURRENT SENSE

The bq2400x regulates current by sensing, on the ISNS pin, the voltage drop developed across an external sense resistor. The sense resistor must be placed between the supply voltage (Vcc) and the input of the IC (IN pins).

VOLTAGE SENSE

To achieve maximum voltage regulation accuracy, the bq2400x uses the feedback on the VSENSE pin. Externally, this pin should be connected as close to the battery cell terminals as possible. For additional safety, a $10k\Omega$ internal pullup resistor is connected between the VSENSE and OUT pins.

ENABLE (EN)

The logic EN input is used to enable or disable the IC. A high-level signal on this pin enables the bq2400x. A low-level signal disables the IC and places the device in a low-power standby mode.



THERMAL INFORMATION

THERMALLY ENHANCED TSSOP-20

The thermally enhanced PWP package is based on the 20-pin TSSOP, but includes a thermal pad (see Figure 20) to provide an effective thermal contact between the IC and the PWB.

Traditionally, surface mount and power have been mutually exclusive terms. A variety of scaled-down TO220-type packages have leads formed as gull wings to make them applicable for surface-mount applications. These packages, however, suffer from several shortcomings: they do not address the very low profile requirements (<2 mm) of many of today's advanced systems, and they do not offer a pin-count high enough to accommodate increasing integration. On the other hand, traditional low-power surface-mount packages require power-dissipation derating that severely limits the usable range of many high-performance analog circuits.

The PWP package (thermally enhanced TSSOP) combines fine-pitch surface-mount technology with thermal performance comparable to much larger power packages.

The PWP package is designed to optimize the heat transfer to the PWB. Because of the very small size and limited mass of a TSSOP package, thermal enhancement is achieved by improving the thermal conduction paths that remove heat from the component. The thermal pad is formed using a lead-frame design (patent pending) and manufacturing technique to provide the user with direct connection to the heat-generating IC. When this pad is soldered or otherwise coupled to an external heat dissipator, high power dissipation in the ultrathin, fine-pitch, surface-mount package can be reliably achieved.

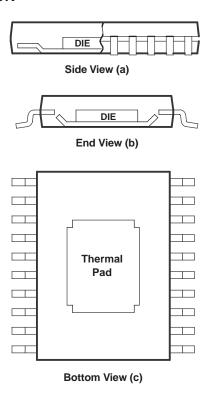


Figure 20. Views of Thermally Enhanced PWP Package

Because the conduction path has been enhanced, power-dissipation capability is determined by the thermal considerations in the PWB design. For example, simply adding a localized copper plane (heat-sink surface), which is coupled to the thermal pad, enables the PWP package to dissipate 2.5 W in free air. (Reference Figure 22(a), 8 cm² of copper heat sink and natural convection.) Increasing the heat-sink size increases the power dissipation range for the component. The power dissipation limit can be further improved by adding airflow to a PWB/IC assembly (see Figure 22(b) and 22(c)). The line drawn at 0.3 cm² in Figures 21 and 22 indicates performance at the minimum recommended heat-sink size.



THERMAL INFORMATION

THERMAL RESISTANCE **COPPER HEAT-SINK AREA** 150 125 **Natural Convection** R_{θ} JA $\,$ – Thermal Resistance – $\,^{\circ}$ C/W 50 ft/min 100 ft/min 100 150 ft/min 200 ft/min 75 50 250 ft/min 300 ft/min 25 1 2 3 4 5 6 7 8 0 0.3 Copper Heat-Sink Area – cm²

Figure 21



THERMAL INFORMATION

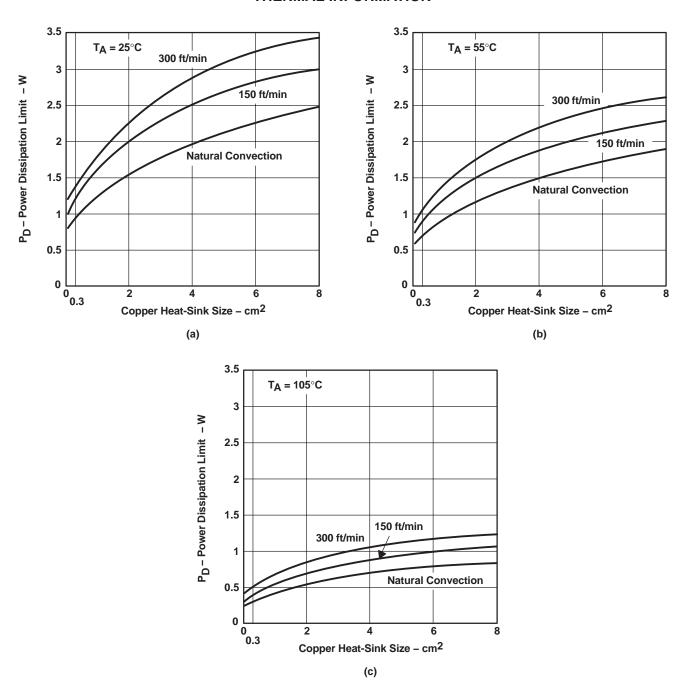


Figure 22. Power Ratings of the PWP Package at Ambient Temperatures of 25°C, 55°C, and 105°C







PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
BQ24001PWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24001PWPG4	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24001PWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24001PWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24001RGWR	ACTIVE	QFN	RGW	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24001RGWRG4	ACTIVE	QFN	RGW	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24002PWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24002PWPG4	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24002PWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24002PWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24002RGWR	ACTIVE	QFN	RGW	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24002RGWRG4	ACTIVE	QFN	RGW	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24003PWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24003PWPG4	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24003PWPR	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24003PWPRG4	ACTIVE	HTSSOP	PWP	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24003RGWR	ACTIVE	QFN	RGW	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24003RGWRG4	ACTIVE	QFN	RGW	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



PACKAGE OPTION ADDENDUM

6-Dec-2006

package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PWP (R-PDSO-G**)

PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE

20 PIN SHOWN

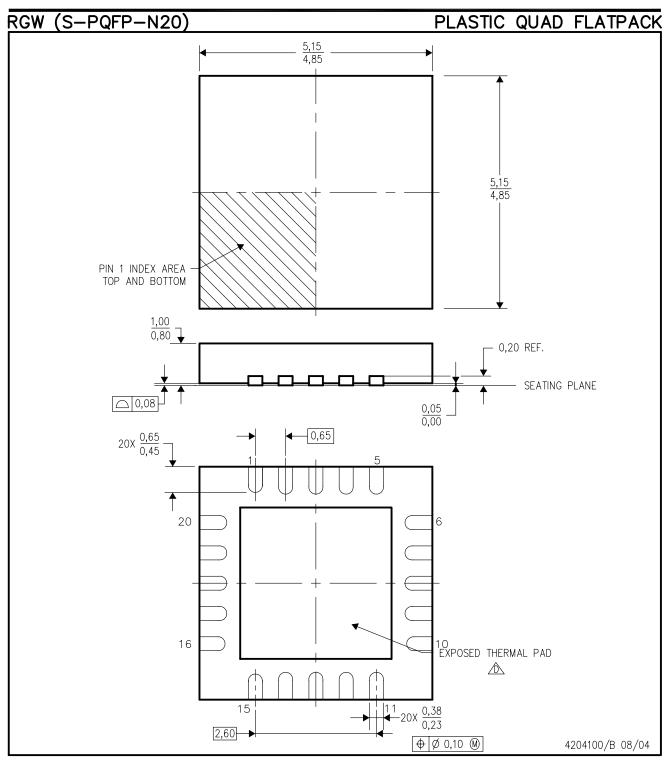


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com www.ti.com.
- E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5—1994.

- B. This drawing is subject to change without notice.
- C. Quad Flat pack, No-leads (QFN) package configuration
- The package thermal pad must be soldered to the board for thermal and mechanical performance..
 - See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
- E. Falls within JEDEC MO-220.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
Low Power Wireless	www.ti.com/lpw	Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

Copyright © 2006, Texas Instruments Incorporated